



STGD10NC60S STGP10NC60S

10 A, 600 V fast IGBT

Features

- Optimized performance for medium operating frequencies up to 5 kHz in hard switching
- Low on-voltage drop ($V_{CE(sat)}$)

Application

- Motor drive

Description

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

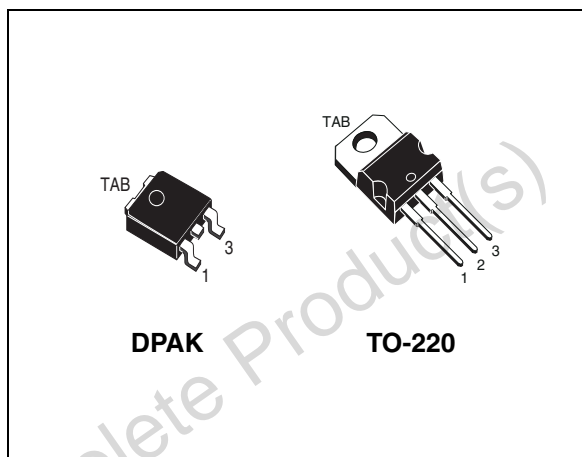


Figure 1. Internal schematic diagram

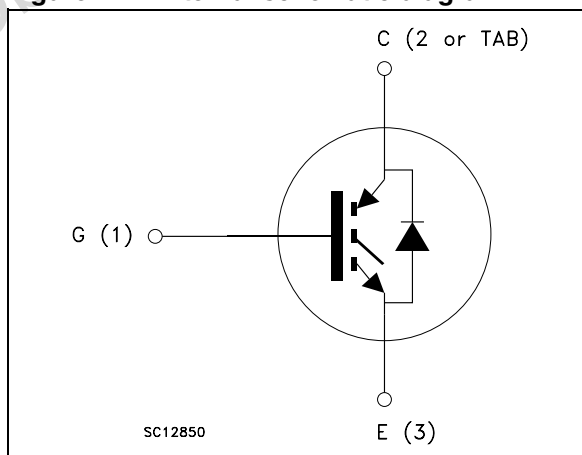


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGD10NC60ST4	GD10NC60S	DPAK	Tape and reel
STGP10NC60S	GP10NC60S	TO-220	Tube

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves)	5
3	Test circuits	8
4	Package mechanical data	9
5	Packaging mechanical data	14
6	Revision history	17

Obsolete Product(s) - Obsolete Product(s)

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		DPAK	TO-220	
V _{CES}	Collector-emitter voltage (V _{GE} = 0)	600		V
I _C ⁽¹⁾	Continuous collector current at T _C = 25°C	18	21	A
I _C ⁽¹⁾	Continuous collector current at T _C = 100°C	10	11	A
I _{CL} ⁽²⁾	Turn-off latching current	14		A
I _{CP} ⁽³⁾	Pulsed collector current	25		A
V _{GE}	Gate-emitter voltage	±20		V
P _{TOT}	Total dissipation at T _C = 25 °C	60	62.5	W
T _j	Operating junction temperature	-55 to 150		°C

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

2. V_{clamp} = 80%.(V_{CES}), T_j = 150 °C, R_G = 10 Ω, V_{GE} = 15 V
 3. Pulse width limited by maximum junction temperature and turn-off within RBSOA

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		DPAK	TO-220	
R _{thJC}	Thermal resistance junction-case	2.08	2	°C/W
R _{thJA}	Thermal resistance junction-ambient	100	62.5	°C/W

2 Electrical characteristics

$T_J = 25\text{ °C}$ unless otherwise specified.

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 1\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 5\text{ A}$ $V_{GE} = 15\text{ V}$, $I_C = 5\text{ A}$, $T_J = 125\text{ °C}$		1.45 1.45	1.65	V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	3.75		5.75	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 600\text{ V}$ $V_{CE} = 600\text{ V}$, $T_J = 125\text{ °C}$			150 1	μA mA
I_{GES}	Gate-emitter leakage ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{ V}$			± 100	nA
g_{fs}	Forward transconductance	$V_{CE} = 15\text{ V}$, $I_C = 5\text{ A}$		3.5		S

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$		365		pF
C_{oes}	Output capacitance		-	44	-	pF
C_{res}	Reverse transfer capacitance			8		pF
Q_g	Total gate charge	$V_{CE} = 480\text{ V}$, $I_C = 5\text{ A}$,		18		nC
Q_{ge}	Gate-emitter charge	$V_{GE} = 15\text{ V}$	-	8	-	nC
Q_{gc}	Gate-collector charge	Figure 16		3.5		nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$ $R_G = 10\text{ }\Omega$, $V_{GE} = 15\text{ V}$, Figure 17		19		ns
t_r	Current rise time		-	4	-	ns
$(di/dt)_{on}$	Turn-on current slope			1330		A/ μs
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$ $R_G = 10\text{ }\Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ °C}$ Figure 17		18		ns
t_r	Current rise time		-	4.5	-	ns
$(di/dt)_{on}$	Turn-on current slope			1000		A/ μs
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$, $R_G = 10\text{ }\Omega$, $V_{GE} = 15\text{ V}$, Figure 17		100		ns
$t_{d(off)}$	Turn-off delay time		-	160	-	ns
t_f	Current fall time			205		ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$, $R_G = 10\text{ }\Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ °C}$ Figure 17		165		ns
$t_{d(off)}$	Turn-off delay time		-	250	-	ns
t_f	Current fall time			310		ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CC} = 480\text{ V}, I_C = 5\text{ A}$		60		μJ
$E_{off}^{(2)}$	Turn-off switching losses	$R_G = 10\ \Omega, V_{GE} = 15\text{ V},$ <i>Figure 15</i>	-	340	-	μJ
E_{ts}	Total switching losses			400		μJ
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CC} = 480\text{ V}, I_C = 5\text{ A}$		90		μJ
$E_{off}^{(2)}$	Turn-off switching losses	$R_G = 10\ \Omega, V_{GE} = 15\text{ V},$ $T_J = 125^\circ\text{C}$ <i>Figure 15</i>	-	540	-	μJ
E_{ts}	Total switching losses			630		μJ

1. E_{on} is the turn-on losses when a typical diode is used in the test circuit in *Figure 15*. If the IGBT is offered in a package with a co-pack diode, the co-pack diode is used as external diode. IGBTs and diode are at the same temperature
2. Turn-off losses included also include also the tail of the collector current

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

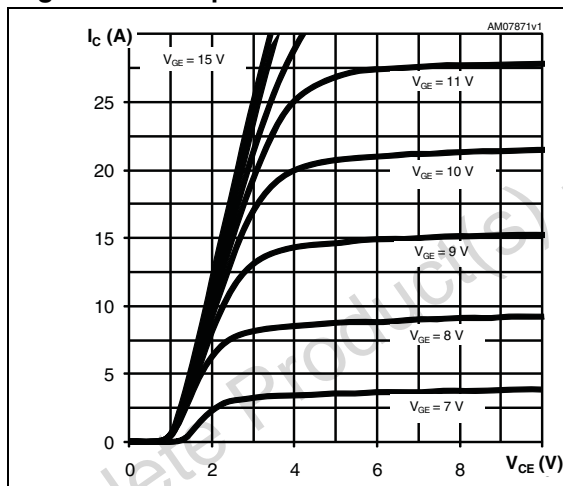


Figure 3. Transfer characteristics

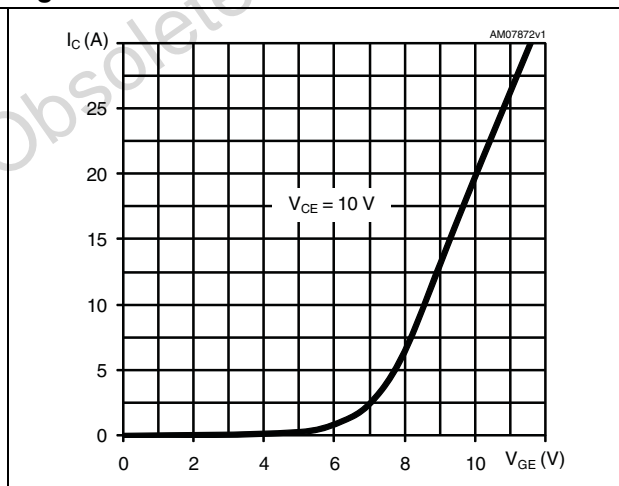


Figure 4. Collector-emitter on voltage vs. collector current

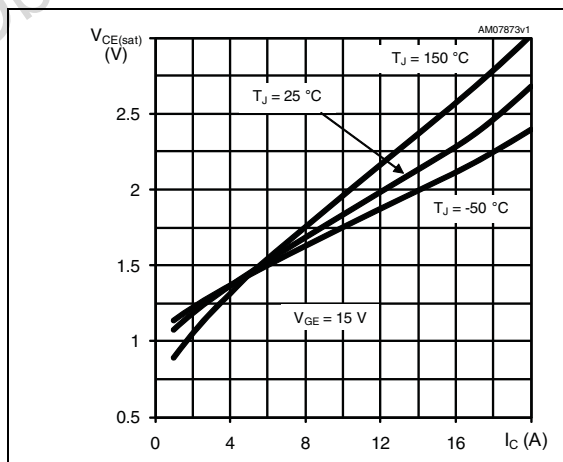


Figure 5. Collector-emitter on voltage vs. temperature

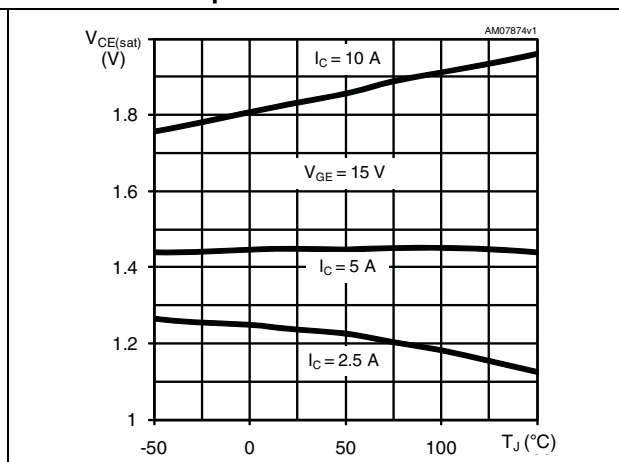


Figure 6. Normalized breakdown voltage vs. temperature

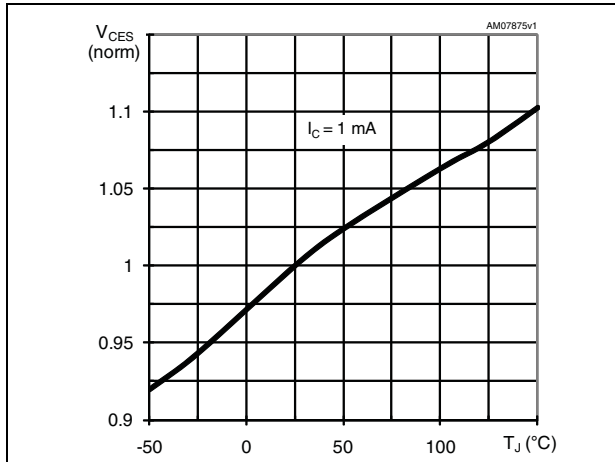


Figure 7. Normalized gate threshold voltage vs. temperature

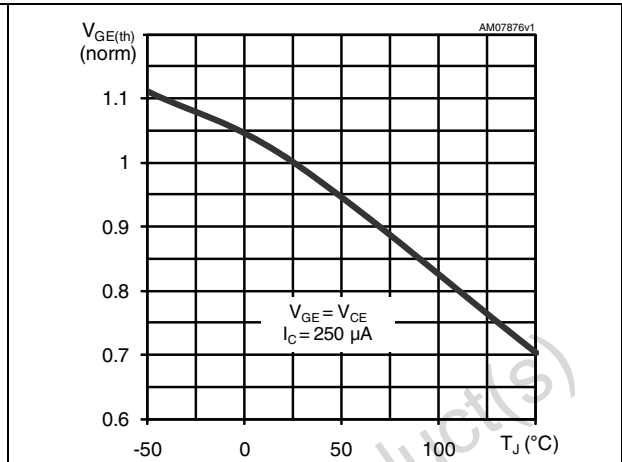


Figure 8. Gate charge vs. gate-emitter voltage

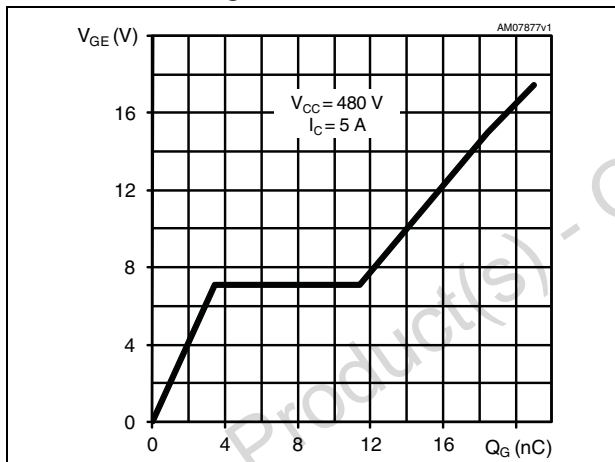


Figure 9. Capacitance variations

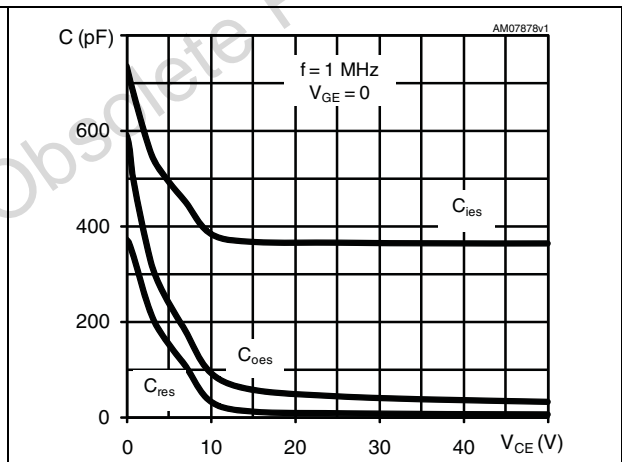


Figure 10. Switching losses vs. temperature

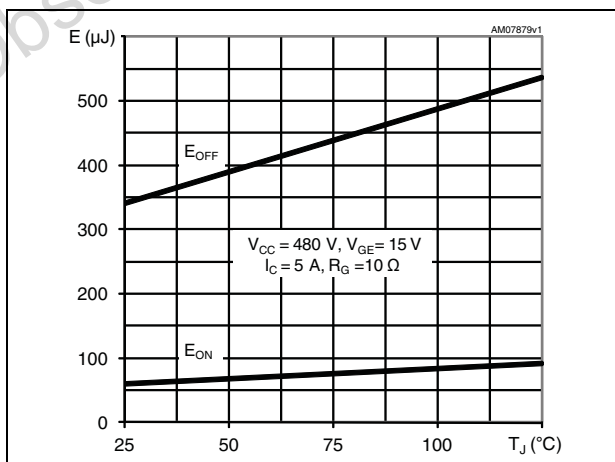


Figure 11. Switching losses vs. gate resistance

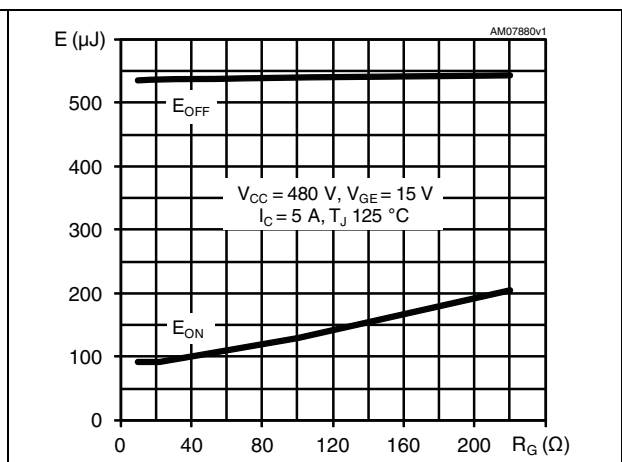


Figure 12. Switching losses vs. collector current

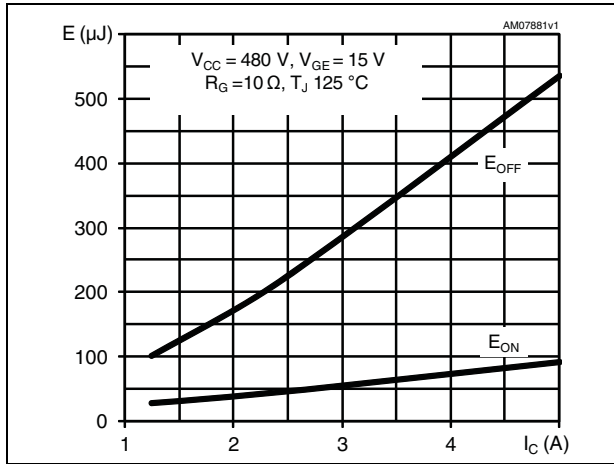


Figure 13. Turn-off SOA

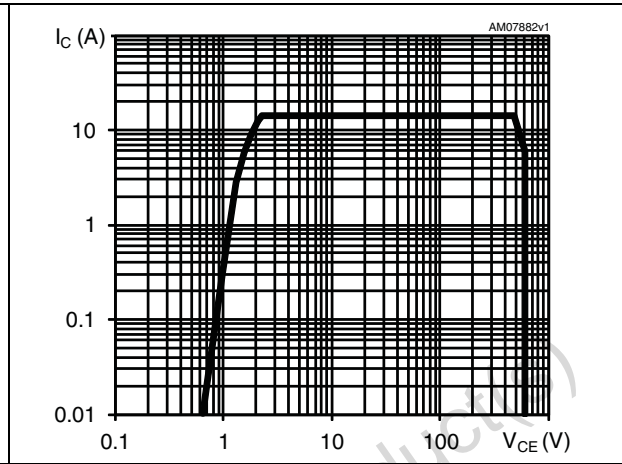
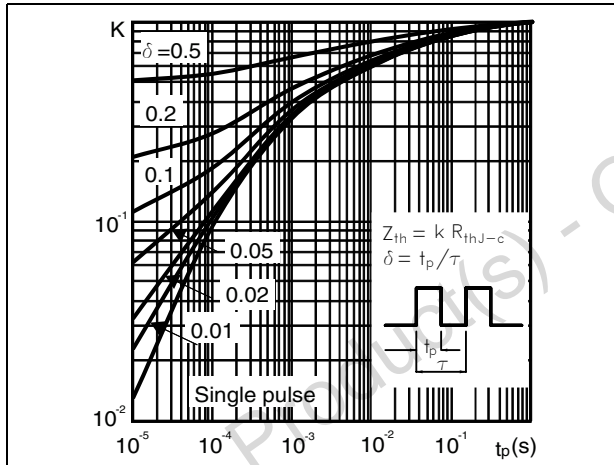


Figure 14. Thermal impedance for DPAK and TO-220



3 Test circuits

Figure 15. Test circuit for inductive load switching

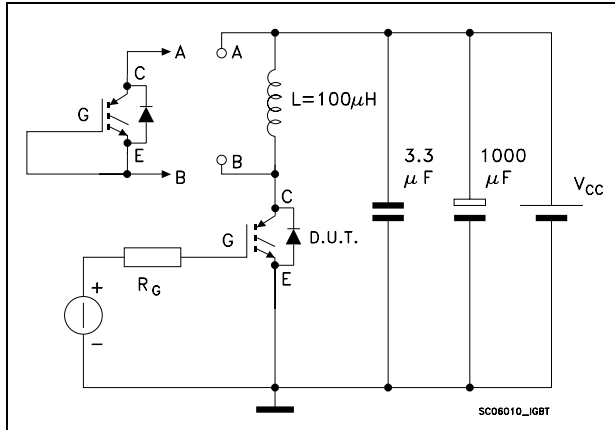


Figure 16. Gate charge test circuit

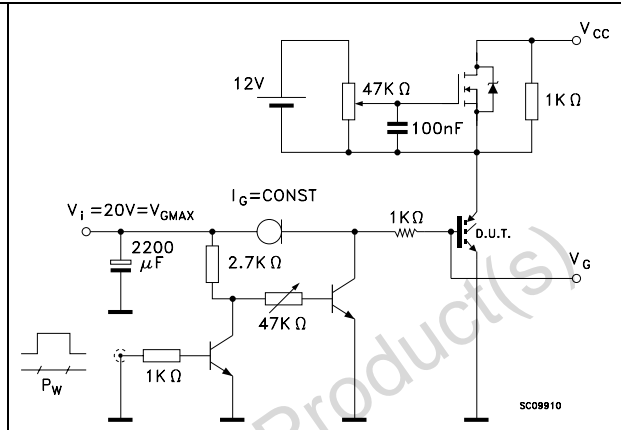
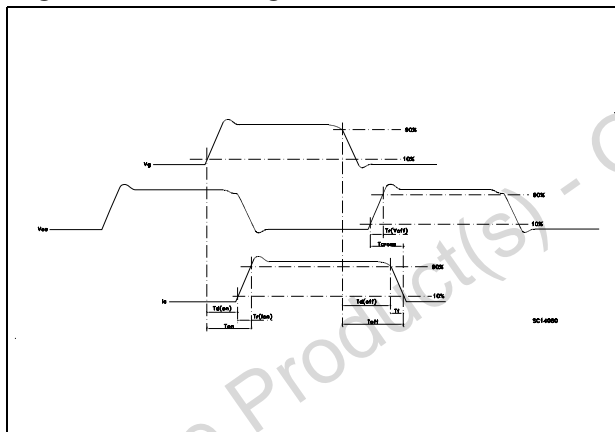


Figure 17. Switching waveforms



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Obsolete Product(s) - Obsolete Product(s)

Table 8. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 18. DPAK (TO-252) drawing

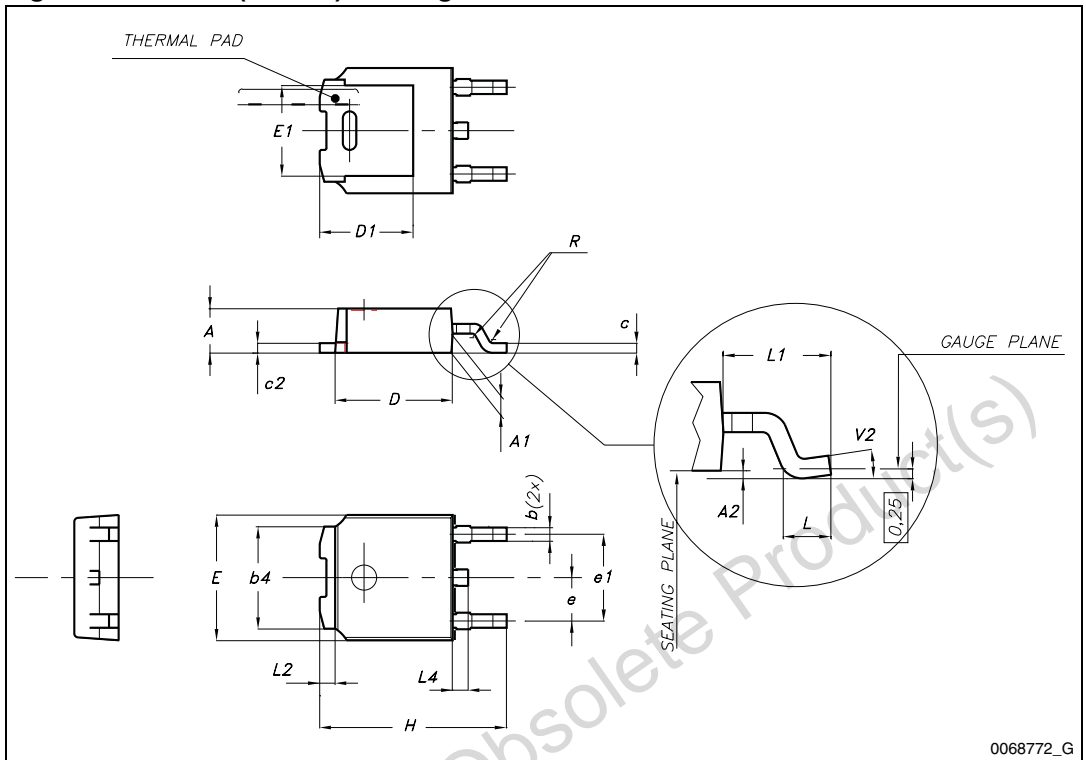
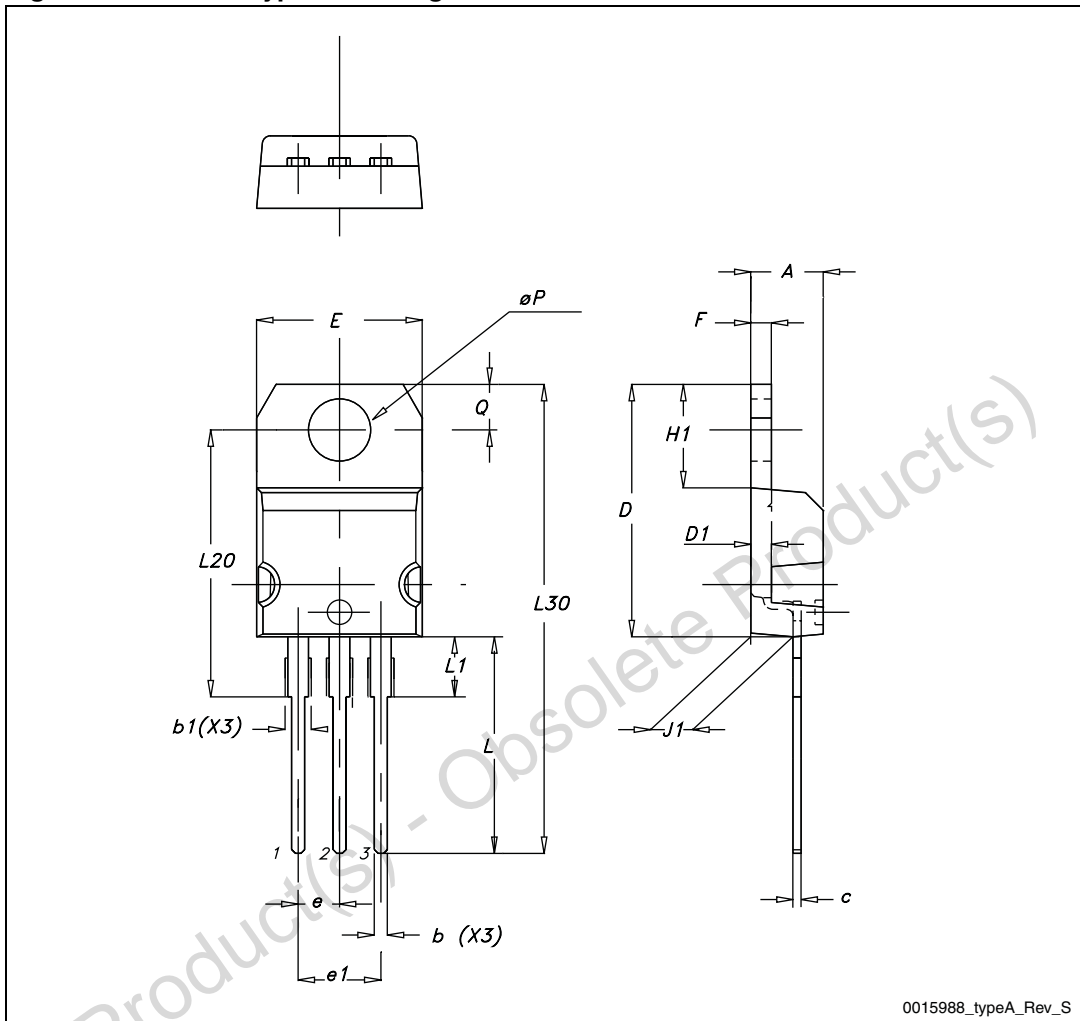


Table 9. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 19. TO-220 type A drawing



0015988_typeA_Rev_S

Figure 21. Tape for DPAK (TO-252)

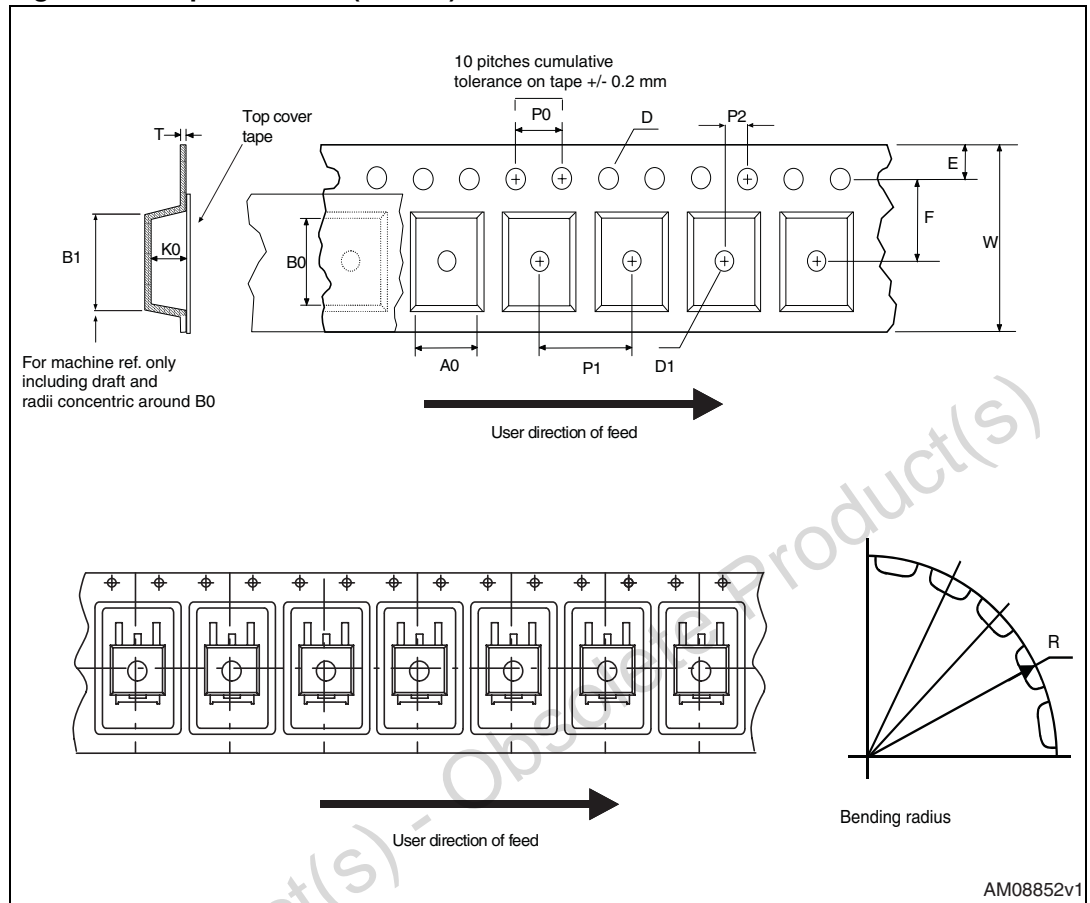
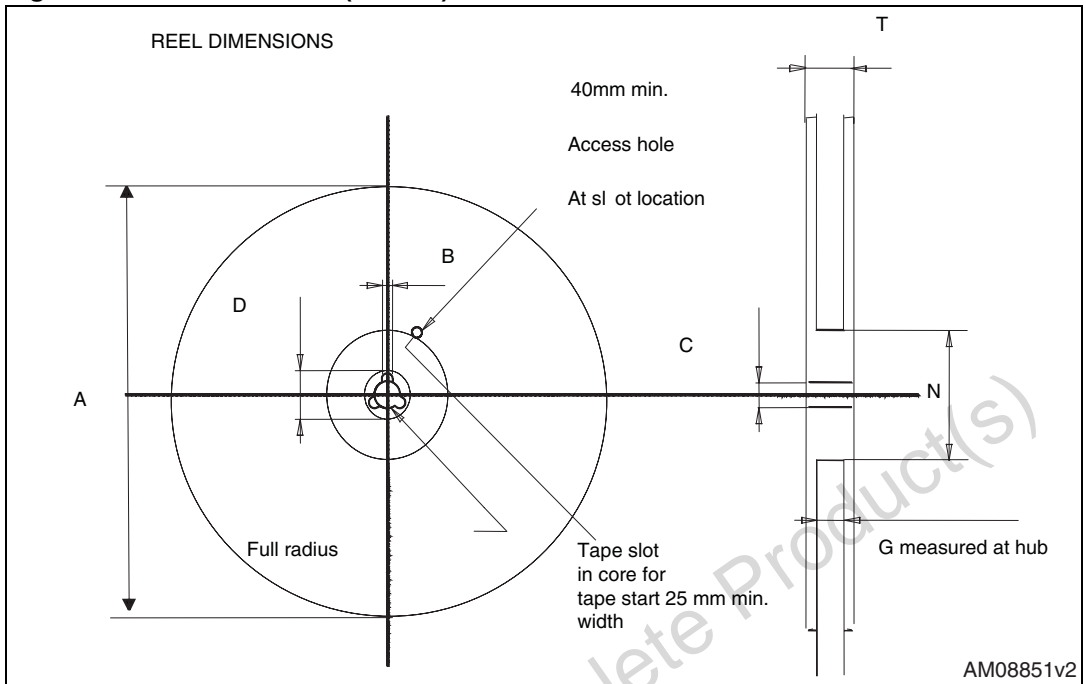


Figure 22. Reel for DPAK (TO-252)



Obsolete Product(s) - Obsolete Product(s)

6 Revision history

Table 11. Document revision history

Date	Revision	Changes
06-Jul-2009	1	Initial release
17-Dec-2010	2	Inserted Section 2.1: Electrical characteristics (curves) on page 5

Obsolete Product(s) - Obsolete Product(s)

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2010 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com